Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- · Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Isolated package
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- · General purpose phase control
- · General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage		600		V		
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 73 °C; Fig. 1; Fig. 2; Fig. 3	8		А		
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	65 A		А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-		2.5	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-		3.5	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-		3.5	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-		6.5	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-		1.5	10	mA

4Q Triad

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		
3	G	gate		T2—T1
mb	n.c.	mounting base; isolated		Sym051

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
BT137X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT137X-600D	BT137X-600D

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak off-state voltage		600	V
RMS on-state current	full sine wave; T _h ≤ 73 °C; Fig 1; Fig 2; Fig 3	8	А
non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	65	Α
	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	71	Α
I ² t for fusing	t _p = 10 ms; SIN	21	A ² s
rate of rise of on-state current	I _G = 10 mA; T2+ G+	50	A/µs
	I _G = 10 mA; T2+ G-	50	A/µs
	I _G = 10 mA; T2- G-	50	A/µs
	I _G = 20 mA; T2- G+	10	A/µs
peak gate current		2	А
peak gate power		5	W
average gate power	over any 20 ms period	0.5	W
storage temperature		-40 to 150	°C
junction temperature		125	°C
	repetitive peak off-state voltage RMS on-state current non-repetitive peak on-state current I²t for fusing rate of rise of on-state current peak gate current peak gate power average gate power storage temperature	repetitive peak off-state voltage RMS on-state current full sine wave; $T_h \le 73$ °C; Fig 1; Fig 2; Fig 3 non-repetitive peak onstate current full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5 full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms $I^2t \text{ for fusing} \qquad t_p = 10 \text{ ms; SIN}$ rate of rise of on-state current $I_G = 10 \text{ mA; T2+ G-}$ $I_G = 10 \text{ mA; T2- G-}$ $I_G = 20 \text{ mA; T2- G-}$ peak gate current peak gate power average gate power average gate power storage temperature	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

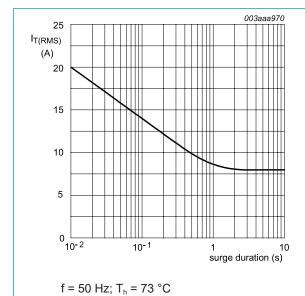


Fig. 1. RMS on-state current as a function of surge duration; maximum values

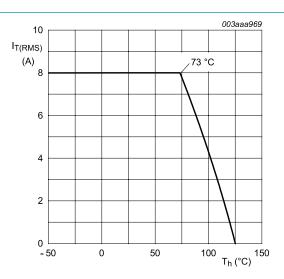
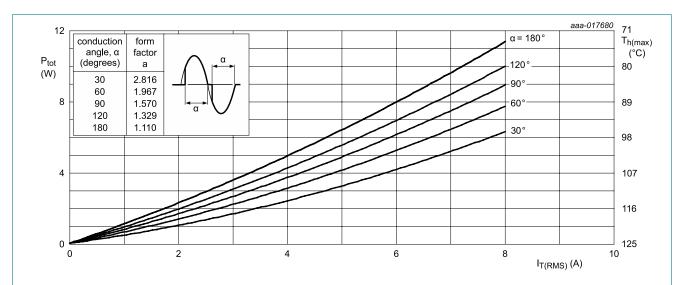


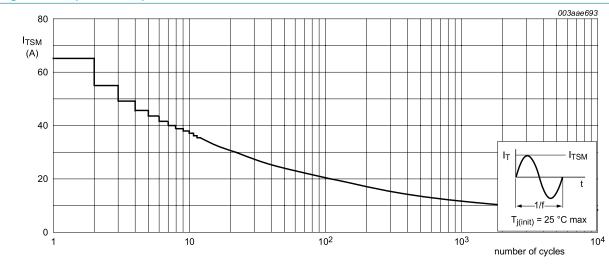
Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



 α = conduction angle

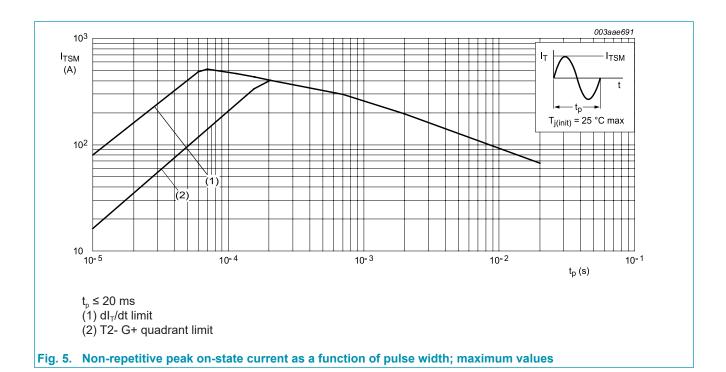
 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

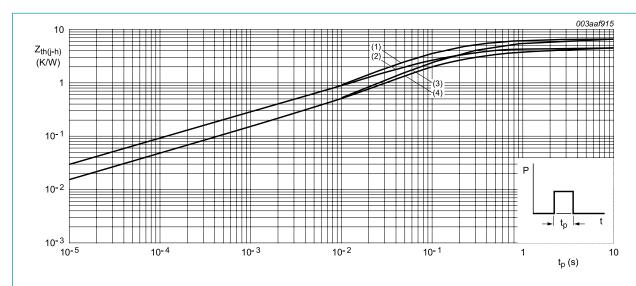
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

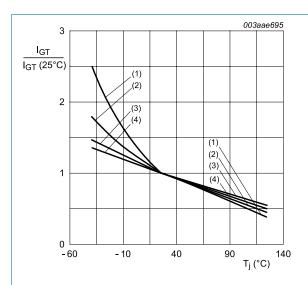
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; $T_h = 25$ °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics				`	
I_{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	3.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	3.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	6.5	10	mA
I _L la	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2+ G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	1.6	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{2}$	-	8.5	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{2}$	-	1.2	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	2.5	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	1.5	10	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		'	,	'	,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform;	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 12 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

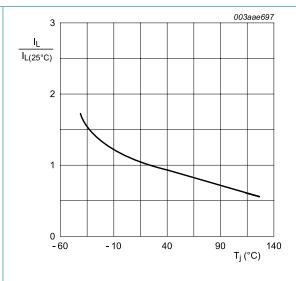


Fig. 8. Normalized latching current as a function of junction temperature

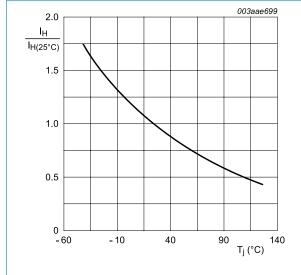
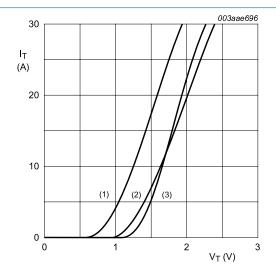


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.264 V; R_s = 0.038 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

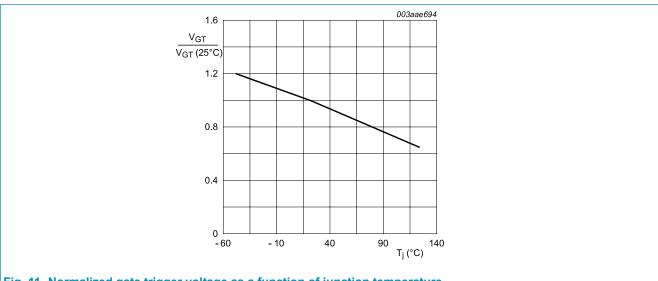
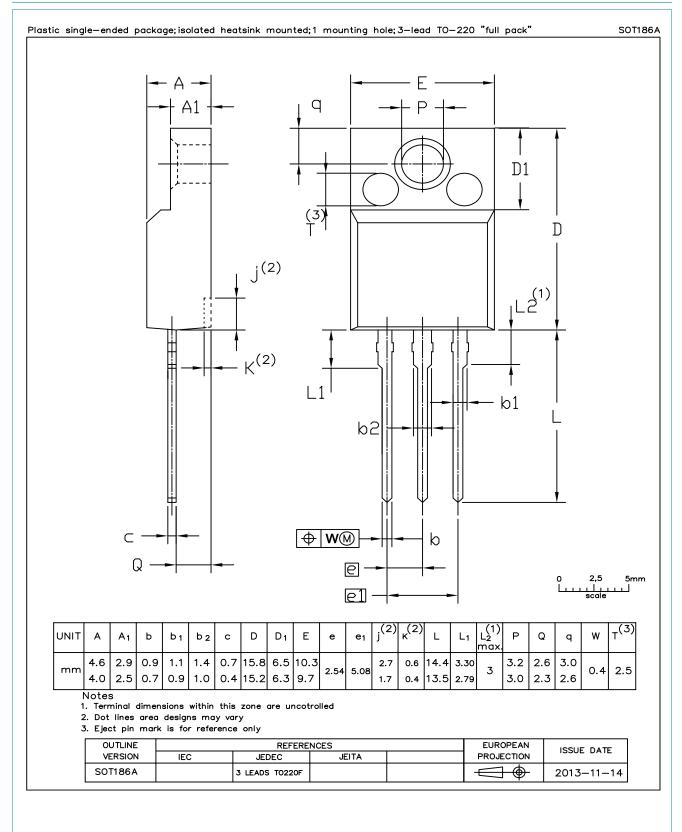


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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14. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	6
10. Isolation Characteristics	6
11. Characteristics	7
12. Package outline	10
13. Legal information	11
14. Contents	13

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